# **2SJ0164** (2SJ164)

### Silicon P-channel junction FET

For switching circuits Complementary to 2SK1104

#### Features

- Low ON resistance
- Low-noise characteristics

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Gate-drain surrender voltage	$V_{GDS}$	65	V
Drain current	$I_D$	-20	mA
Gate current	$I_G$	-10	mA
Power dissipation	$P_{\mathrm{D}}$	300	mW
Channel temperature	T <sub>ch</sub>	150	> °C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C/

#### Package

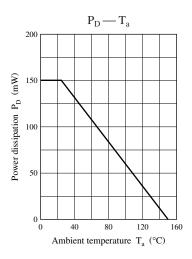
<ul> <li>Features</li> <li>Low ON resistance</li> <li>Low-noise characteristics</li> </ul> Absolute Maximum Rating	is $T_a = 2$	5°C	■ Pack • Code • NS-A • Pin Na 1: Sou	tage  I ame	Line	ins.			
Parameter	Symbol	Rating	Unit 2: Gate	rce W					
Gate-drain surrender voltage	V <sub>GDS</sub>	65	V 3: Dra	j), '(c)					
Drain current	$I_D$	-20	V mA mA mW	97					
Gate current	$I_G$	-10	mA C		~6				
Power dissipation	$P_{\mathrm{D}}$	300	mW CO		KILO				
Channel temperature	T <sub>ch</sub>	150	S.c. N	(	<b>)</b> ,				
Storage temperature	T <sub>stg</sub>	-55 to + <b>1</b> 50	C.C.	163					
Parameter, 0	Symbo		onditions	Min	Тур	Max	Unit		
Gate-drain surrender Voltage	GDS	$I_G = 10 M$	$V_{DS} = 0$	65			V		
Drain-source curren	O I <sub>DSS</sub>	$V_{DS} = -10$	$V, V_{GS} = 0$	- 0.6		-6.0	mA		
Gate-source cutoff current	$\mathbf{I}_{\mathrm{GSS}}$	$V_{GS} = 30 \text{ V}$	$V, V_{DS} = 0$			10	nA		
Gate-source cutoff voltage	V <sub>GS</sub> Q	$V_{DS} = -10$	$V, I_D = -10 \mu A$		1.5	3.5	V		
Mutual conductance	$g_{\rm m}$	$V_{DS} = -10$	$V, I_D = -1 \text{ mA}, f = 1 \text{ kHz}$	1.8	2.5		mS		
Short-circuit forward transfer capacitan (Common source)	C <sub>iss</sub>	$V_{\rm DS} = -10$	$V$ , $V_{GS} = 0$ , $f = 1$ MHz		10		pF		
Reverse transfer capacitance (Common source)	C <sub>rss</sub>				3		pF		
Drain-source ON resistance	R <sub>DS(on)</sub>	$V_{DS} = -10$	$mV, V_{GS} = 0$		300		Ω		

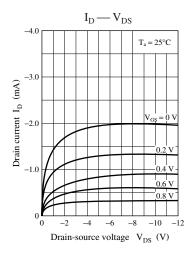
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

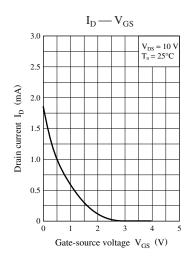
- 2. Observe precautions for handling. Electrostatic sensitive devices.
- 3. \*: Rank classification

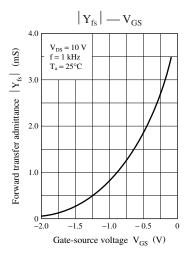
Rank	Р	Q	R
I <sub>DSS</sub> (mA)	- 0.6 to -1.5	−1.0 to −3.0	-2.5 to -6.0

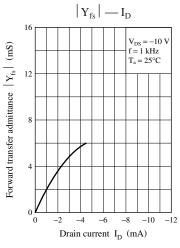
Note) The part number in the parenthesis shows conventional part number.

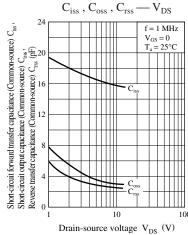






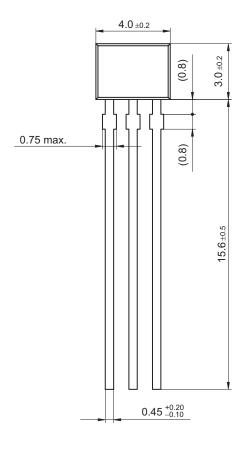


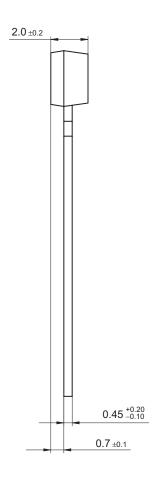


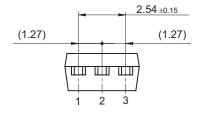


2 SJF00002CED

NS-A1 Unit: mm







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